

## NTE586 Silicon Rectifier Diode Schottky Barrier, Fast Switching

## **Features:**

- Low Switching Noise
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Capability

<u>Maximum Ratings and Electrical Characteristics:</u>  $(T_A = +25^{\circ}C \text{ unless otherwise specified.}$  Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Maximum Recurrent Peak Reverse Current       40V         Maximum RMS Voltage       28V
Maximum DC Blocking Voltage
Maximum Average Forward Rectified Current (375" . (9.5mm) lead length at $T_L = +95$ °C) 3.0A
Peak Forward Surge Current
(8.3ms single half sine-wave superimposed on rated load $T_L = +75$ °C) 80A
Maximum Instantaneous Forward Voltage at 3A DC (Note 1)
Maximum Average Reverse Current at Rated DC Blocking Voltage
$T_A = +25^{\circ}C$
$T_A = +100^{\circ}C$
Typical Thermal Resistance, Junction-to-Ambient (Note 2), R <sub>thJA</sub>
Typical Junction Capacitance (Note 3)
Operating Junction Temperature Range T <sub>J</sub> 65° to +125°C
Storage Temperature Range T <sub>STG</sub> 65° to +125°C

- Note 1. measured at Pulse Width 300µs, Duty Cycle 2%.
- Note 2. Thermal Resistance Junction to Ambient Vertical PC Board Mounting, 0.5" (12.7mm) Lead Length.
- Note 3. Measured at 1MHz and applied reverse voltage of 4.0 Volts.

